## **AMENDMENTS TO THE SPECIFICATION**

Please replace paragraph [0035] of the instant published application with the following amended paragraph:

[0035] Besides the substrate regions 3, 4, and 5 the substrate 2 has connecting regions 30 and 31 formed between the substrate regions (also cf. FIG. 2). The substrate regions 3 and 4 are connected such that they can move relative to one another e.g. via the connecting region 30. The connecting region 30 functions as it were as an articulated joint or hinge, so that the substrate regions 3 and 4 can also be oriented with respect to one another to form an angle other than  $\frac{1800}{180^{\circ}}$  (correction angle). By way of example, this prevents a deformation of the substrate region 3 from continuing into the substrate region 4. By way of example, if the substrate region 3 is tilted through an angle [[a]]  $\underline{\alpha}$  (illustrated in greatly enlarged and exaggerated fashion in FIG. 1) with respect to the horizontal H due to deformations on account of thermally induced stresses, it is possible, by correspondingly tilting the substrate region 4 in the opposite sense, to avoid a propagation of said angle [[a]]  $\underline{\alpha}$  into the substrate region 4 and even to compensate for the tilting by means of an equal and opposite tilting. A module underside 25 which is free to the greatest possible extent from deformations manifested on account of thermally induced stresses is thus provided as contact area of the power semiconductor module.